

Features

- 200 Watts Peak Pulse Power per Line (tp = 8/20μs)
- Bidirectional Configuration
- Protects One Power or I/O Port
- ESD Protection > 40 kilovolts
- Low Clamping Voltages



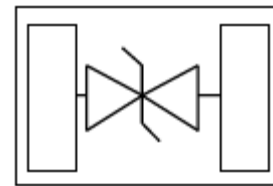
DFN1006

IEC Compatibility (EN61000-4)

- IEC 61000-4-2 (ESD) :±30kV (air), ±30kV (contact)
- IEC 61000-4-4 (EFT) :40A (5/50ns)
- IEC 61000-4-5(Surge): 18A, 8/20μs

Applications

- Ethernet - 10/100/1000 Base T
- Cellular Phones
- Handheld - Wireless Systems
- Personal Digital Assistant (PDA)
- USB Interface

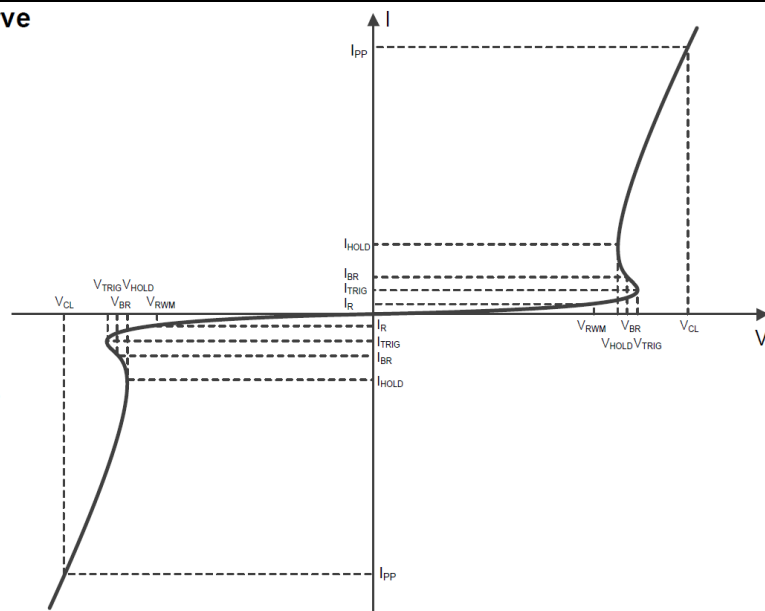


Electrical Parameters

Parameter	Symbol	Value	Units
Peak pulse power (tp=8/20us)	P _{PP}	200	Watts
Operating Temperature	T _J	-55 °C ~125 °C	°C
Storage Temperature	T _{STG}	-55 °C ~150 °C	°C

Electrical performance curve

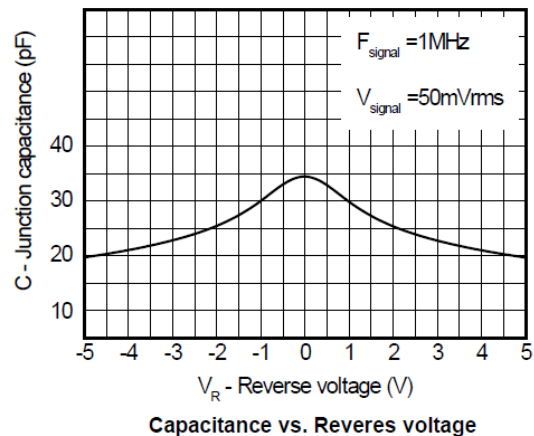
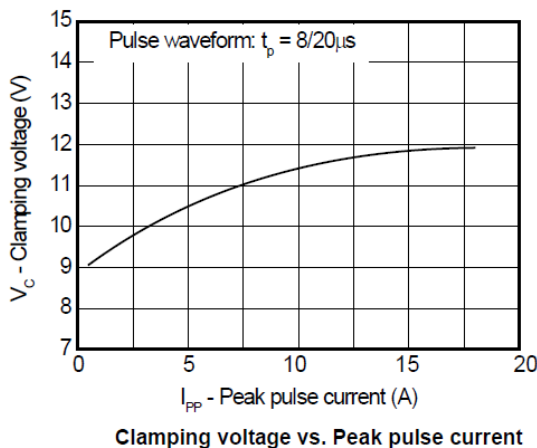
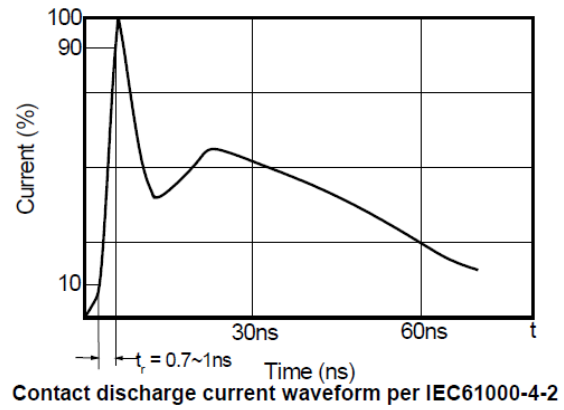
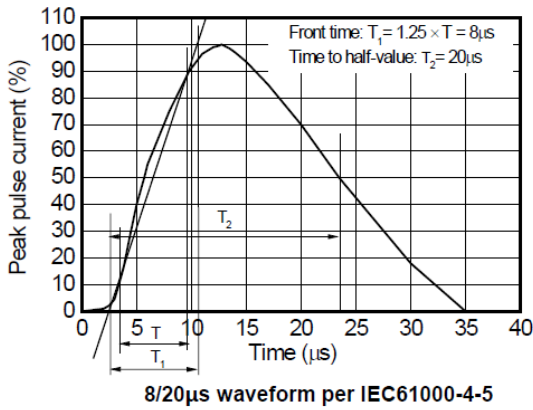
- V_{RWM} Reverse stand-off voltage
- I_R Reverse leakage current
- V_{CL} Clamping voltage
- I_{PP} Peak pulse current
- V_{TRIG} Reverse trigger voltage
- I_{TRIG} Reverse trigger current
- V_{BR} Reverse breakdown voltage
- I_{BR} Reverse breakdown current
- V_{HOLD} Reverse holding voltage
- I_{HOLD} Reverse holding current

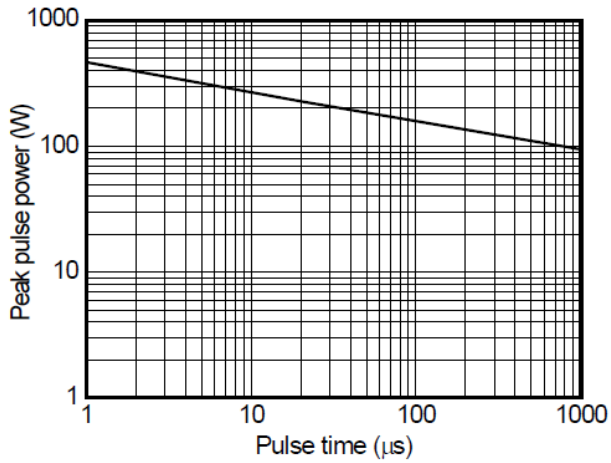


Ratings and characteristic curves ($T_A=25^{\circ}C$ unless otherwise noted)

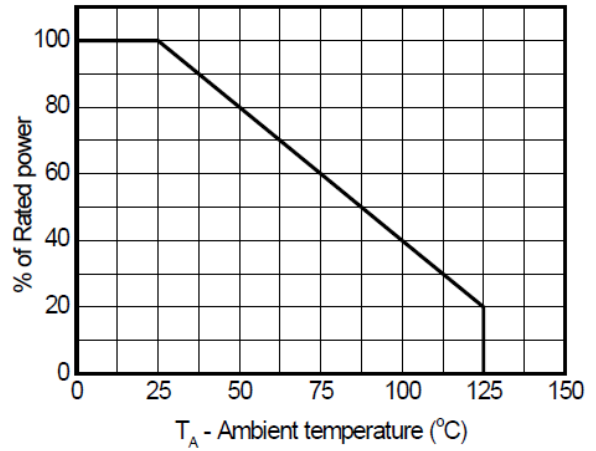
Parameter	Symbol	Condition	Min	Max	Units
Reverse Stand-off Voltage	V_{RWM}	Pin2 to 1/Pin1 to 2		5.0	V
Reverse Breakdown Voltage	$V_{BR}(\text{min})$	$I_Z=1\text{mA}$	5.5	8.0	V
Reverse Leakage Current	$I_R(\text{max})$	@ V_{RWM}		0.2	μA
Clamping Voltage	V_C	$I_{PP}=18\text{A}$ $t_p=8/20\mu\text{s}$		12	V
Peak Pulse Current	I_{PP}	$t_p=8/20\mu\text{s}$	18		A
Junction Capacitance	$C_{I/O}$	Pin capacitance to GND. $V_{dc}=0\text{V}, f=1\text{MHZ}$		40	pf

Typical Characteristics





Non-repetitive peak pulse power vs. Pulse time



Power derating vs. Ambient temperature

Dimensions

DFN1006

DIMENSION OUTLINE:

Unit:mm

